**Attachement 1**

**ORDER DESCRIPTION**

1. **Object of the contract**

The subject of the order is the supply of semiconductors wafers listed below by name and quantity needed:

1. GaAs N-type 3” 100 pieces

2. GaAs N-type 4” (100mm) 100 pieces

3. GaAs N-type 6“ (150mm) 50 pieces

1. **The scope of the subject of the contract**

A detailed description of the subject of the contract is provided in section 5 of this document.

1. **Criterion**

Offers will be evaluated according to a point scale with a maximum number of points of 100.

|  |  |  |
| --- | --- | --- |
| Criterion | Maximum number of points S | Method of awarding points |
| Net price (P) | 100 | S x Pmin/Pi |

Where:

* Pi – net price of goods with delivery - for the given offer
* Pmin - the minimum delivery net price for the ordered goods from all offers submitted
* S – number of points

The final score will be calculated by adding up the partial components and then rounded to two decimal places. (rounded from "5" up)

1. **Deadline for completing the order**

Up to 7 weeks from the date of order.

1. **Parameters**

|  |  |  |
| --- | --- | --- |
| Product name | Parametrer | Specification |
| **GaAs N-type**  | Diameter 3” Thickness: 625±25 µm Diameter: 76.2±0.1 mm | Grade: | Prime, Epi-ready |
| Dopant | Si |
| Orientation: | (100)±0.1o |
| Primary Flat: | EJ (0-1-1) ±1o |
| Secondary Flat | EJ (0-11) ±2o |
| Diameter 4”Thickness: 625±25 µmDiameter: 100±0.1 mm | Carrier Conc.: | 0.8-4 E18/cm3 |
| EPD (Average): | 500/cm2 max |
| TTV: | 5 micr. max |
| TIR: | 4 micr. max |
| Diameter 6”Thickness: 675±25 µmDiameter: 150±0.1 mm | Warp: | 10 micr. max |
| Off-orientation | No miscut |
| Surface Finish: | DSP (double side polished)  |
| Packaging: | ePAK, individual box, sealed with N2 in a moisture-stopping metallic foil bag, done in class 100 clean room. |